

# **SB20W03P**

Schottky Barrier Diode (Twin Type - Cathode Common)

# **30V, 2A Rectifier**

### **Applications**

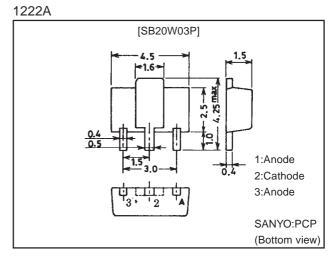
• High frequency rectification (switching regulators, converters, choppers).

#### **Features**

- · Low forward voltage ( $V_F$  max=0.55V).
- $\cdot$  Fast reverse recovery time (trr max=20ns).
- · Low switching noise.
- Low leakage current and high reliability due to highly reliable planar structure.

### Package Dimensions

unit:mm



## **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C (Value per element)

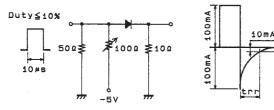
Parameter	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>		30	V
Nonrepetitive Peak Reverse Surge Voltage	VRSM		35	V
Average Output Current	lo		2	A
Surge Forward Current	IFSM	50Hz sine wave, 1 cycle	20	A
Junction Temperature	Tj		-55 to +125	°C
Storage Temperature	Tstg		-55 to +125	°C

#### **Electrical Characteristics** at Ta = 25°C (Value per element)

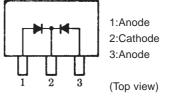
Parameter		Conditons	Ratings			Unit
	Symbol		min	typ	max	
Reverse Voltage	V <sub>R</sub>	I <sub>R</sub> =500μA	30			V
Forward Voltage	VF	I <sub>F</sub> =2A			0.55	V
Reverse Current	IR	V <sub>R</sub> =15V			100	μA
Interterminal Capacitance	С	V <sub>R</sub> =10V, f=1MHz		70		pF
Reverse Recovery Time	trr	I <sub>F</sub> =I <sub>R</sub> =100mA, See specifaied Test Circuit.			20	ns
Thermal Resistance	Rth(j-a) (1)			280		°C/W
	Rth(j-a) (2)	Mounted on 250mm <sup>2</sup> ×0.8mm ceramic board		100		°C/W

#### · Marking:SK

#### trr Test Circuit



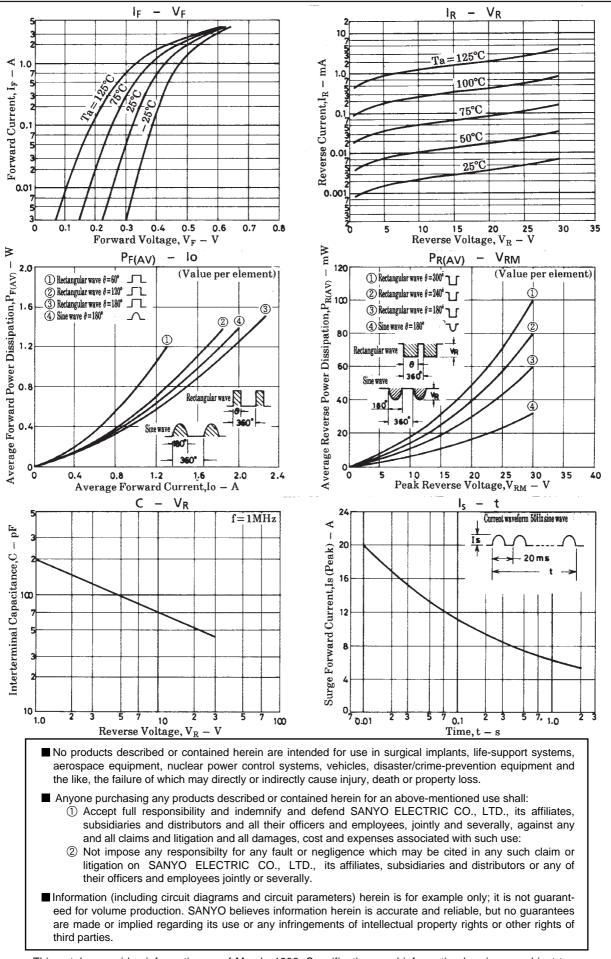
#### **Electrical Connection**



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This catalog provides information as of March, 1998. Specifications and information herein are subject to change without notice.